

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated SCR with sensitive gate in a SOT223 (SC-73) surface mountable plastic package. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

3. Applications

- Adapters
- · Battery powered applications
- Industrial automation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		[1]	-	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5		-	-	10	А
$I_{T(AV)}$	average on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1</u>		-	-	0.6	А
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{sp} \le 112 ^{\circ}\text{C}$; Fig. 2; Fig. 3		-	-	1	A
Static char	acteristics						,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$		-	50	200	μA

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the thyristor may switch to the on-state.





SCR

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	4	A - ▶ - K
2	Α	anode		G sym037
3	G	gate		
4	mb	mb; connected to anode	☐1 ☐2 ☐3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT148W-600R	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
BT148W-600R	BT148W 60

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		[1]	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1</u>		-	0.6	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{sp} \le 112 ^{\circ}\text{C}$; Fig. 2; Fig. 3		-	1	Α
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5		-	10	A
		half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 8.3 \text{ms}$		-	11	A
l ² t	I ² t for fusing	t _p = 10 ms; SIN		-	0.5	A ² s
dI _T /dt	rate of rise of on-state current	Ι _G = 400 μΑ		-	100	A/µs
I _{GM}	peak gate current			-	1	Α
V_{RGM}	peak reverse gate voltage			-	5	V
P_GM	peak gate power			-	1.2	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.12	W
T _{stg}	storage temperature			-40	150	°C
Tj	junction temperature		[2]	-	125	°C

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the thyristor may switch to the on-state.

^[2] Operation above 110°C may require the use of a gate to cathode resistor of $1k\Omega$ or less.

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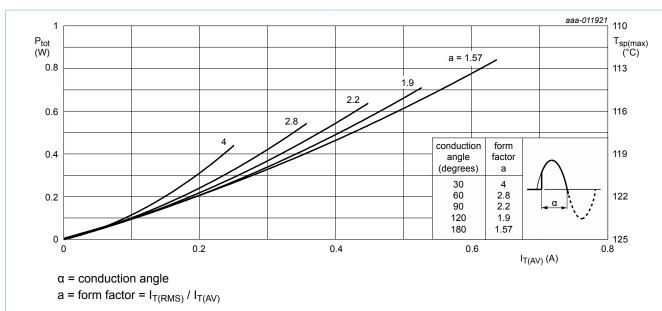


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

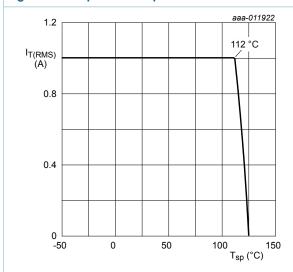
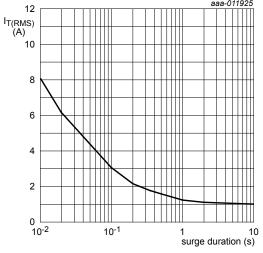


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



f = 50 Hz; T_{sp} = 112 °C

Fig. 3. RMS on-state current as a function of surge duration; maximum values

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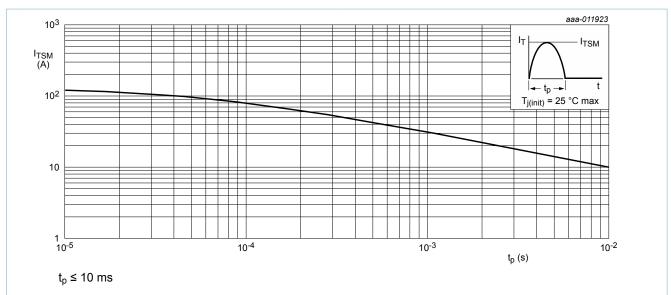


Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

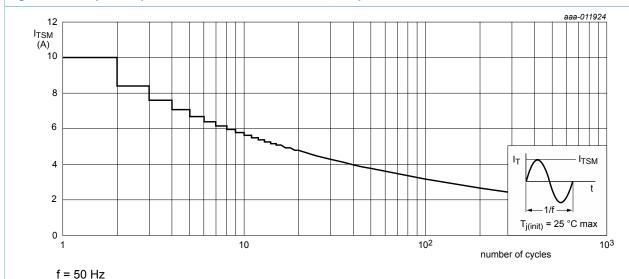


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	Fig. 6	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	printed circuit board mounted; pad area; Fig. 7	-	70	-	K/W
	ambient	printed circuit board mounted; minimum footprint; Fig. 8	-	156	-	K/W

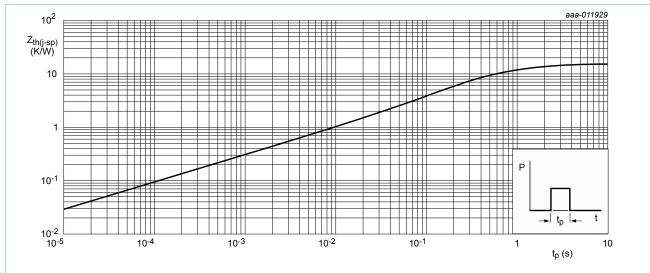
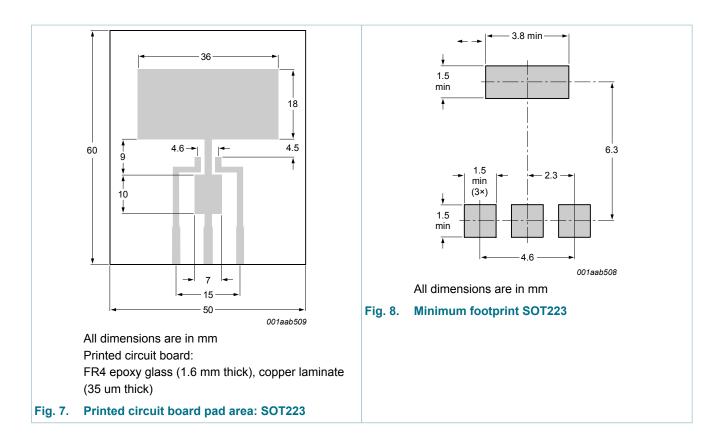


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mir	т Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 9</u>	-	50	200	μA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10	-	0.17	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	0.1	6	mA
V _T	on-state voltage	I _T = 2 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.4	1	V
		$V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 13	0.1	0.2	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
I _R	reverse current	V _R = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics			'		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GK} = 100 Ω; (V_{DM} = 67% of V_{DRM}); exponential waveform; Fig. 14	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 4 \text{ A}; V_D = 600 \text{ V}; I_G = 5 \text{ mA}; dI_G/$ $dt = 0.2 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 402 V; T_j = 125 °C; I_{TM} = 4 A; V_R = 35 V; $(dI_T/dt)_M$ = 30 A/ μ s; dV_D/dt = 2 V/ μ s; R_{GK} = 1 k Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

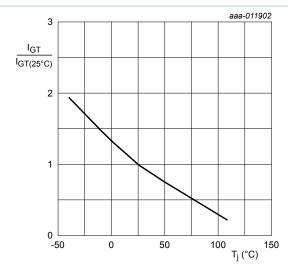


Fig. 9. Normalized gate trigger current as a function of junction temperature

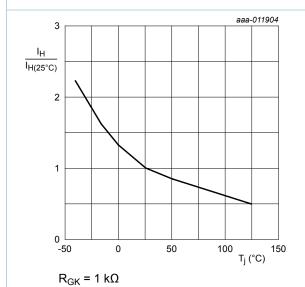
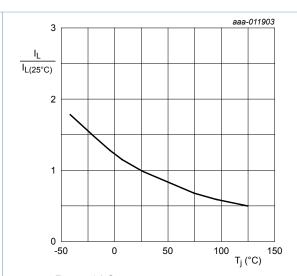
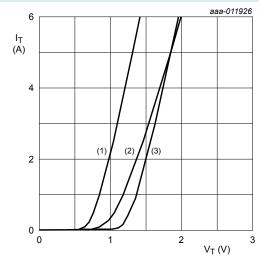


Fig. 11. Normalized holding current as a function of junction temperature



 $R_{GK} = 1 k\Omega$

Fig. 10. Normalized latching current as a function of junction temperature



 $V_0 = 1.107 \text{ V}; R_s = 0.14 \Omega$

(1) T_j = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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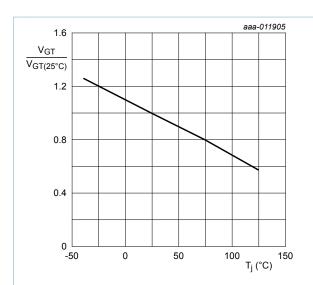


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

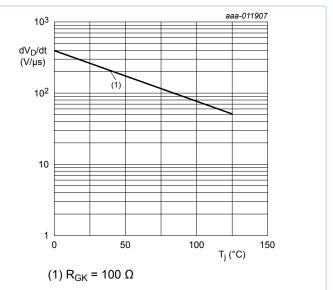
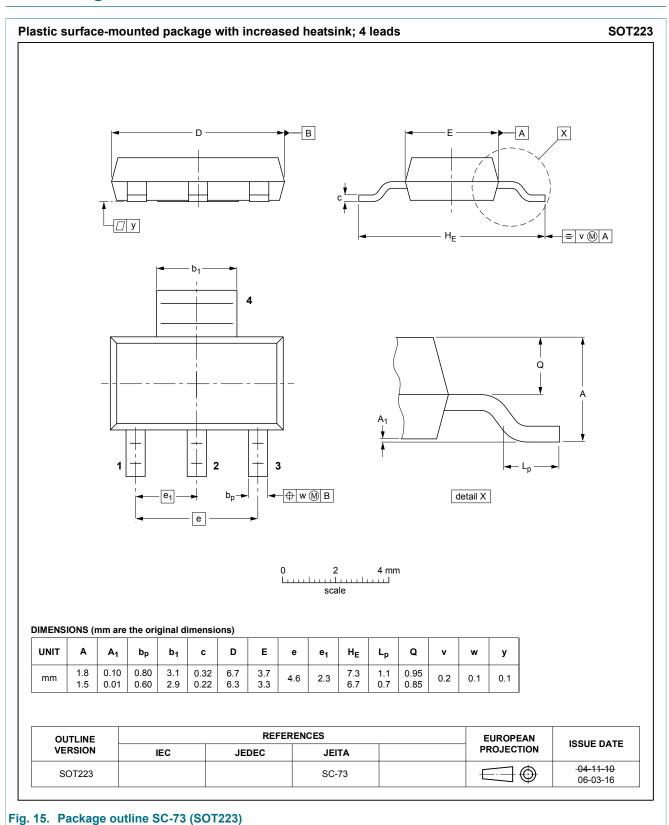
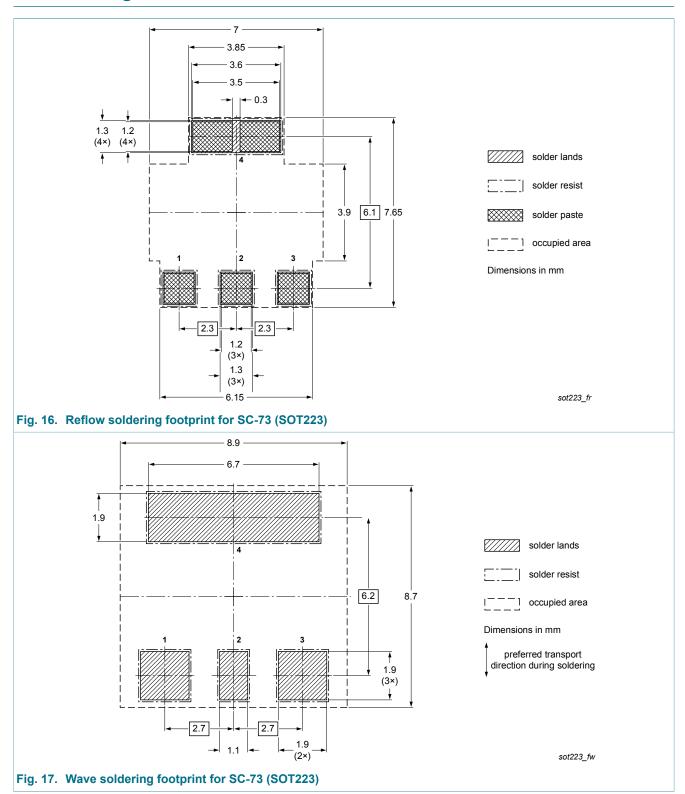


Fig. 14. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

11. Package outline



12. Soldering



13. Legal information

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